# **LINE** DEVICES and more...

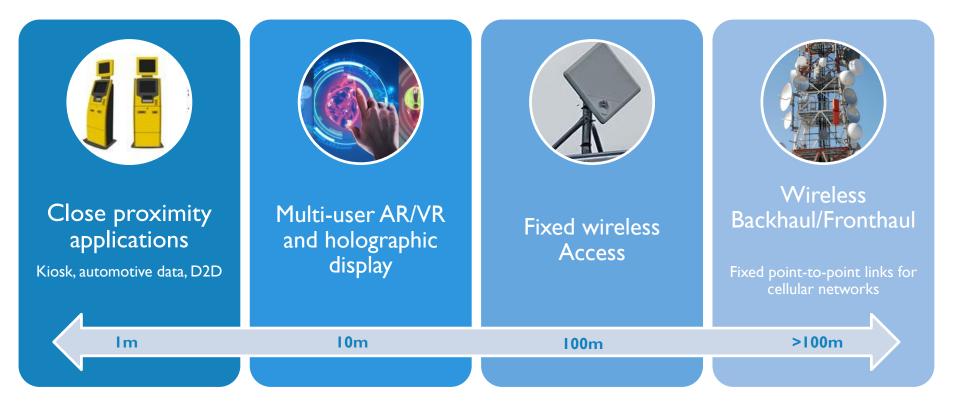
André Bourdoux

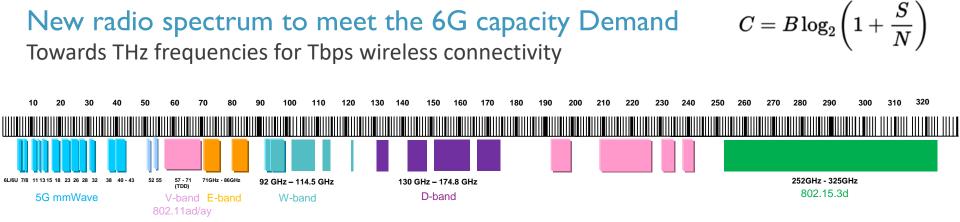
2<sup>nd</sup> Vision for Future Communications Systems 27 - 28 November 2019, University Institute of Lisbon (ISCTE-IUL)

#### Technologies for Communications above 100GHz

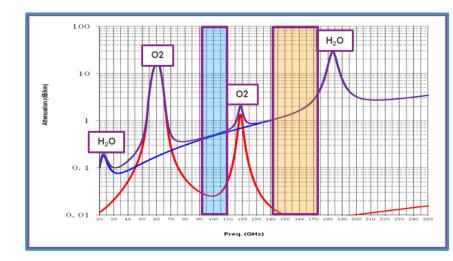
#### B5G/6G high capacity applications

Towards Terabit-Per-second wireless connectivity

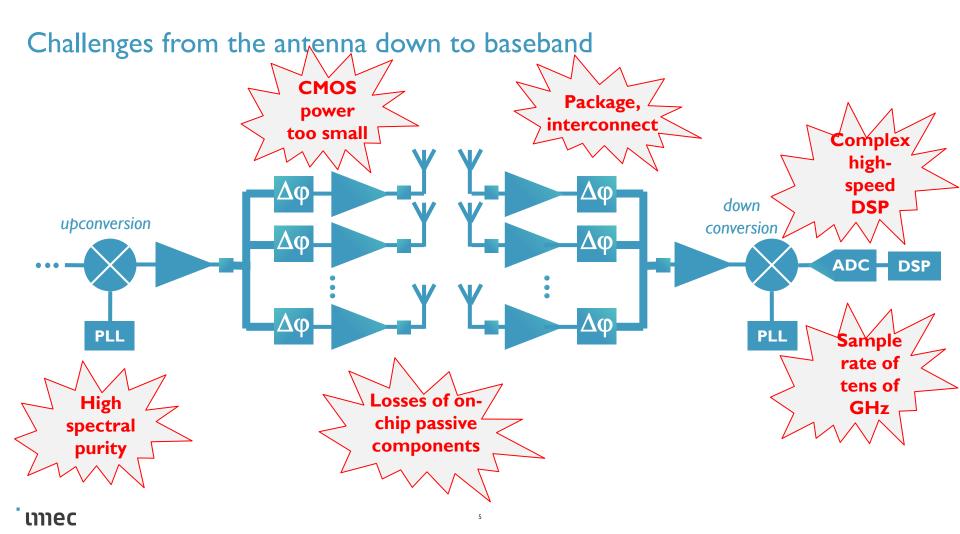




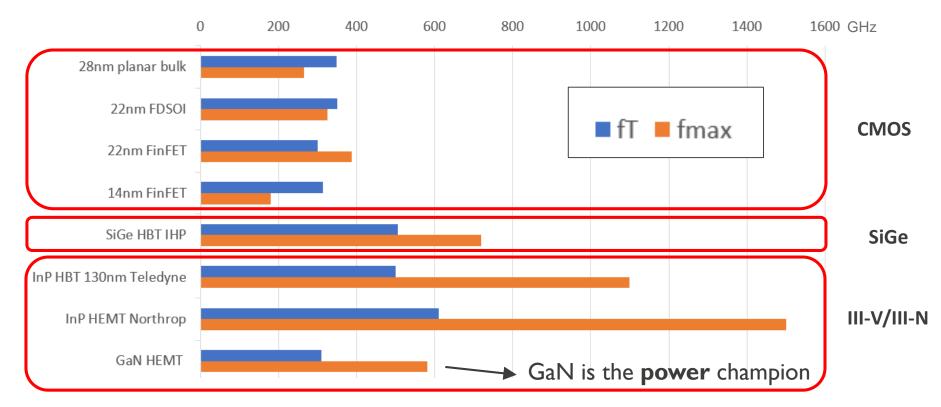
- Wide bandwidths available at higher frequencies
  - W-band: >17GHz
  - D-band: > 30GHz
  - 802.15.3d: > 50GHz



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## For THz range and high power, CMOS is saturating. The champions are the III-V/III-N devices`

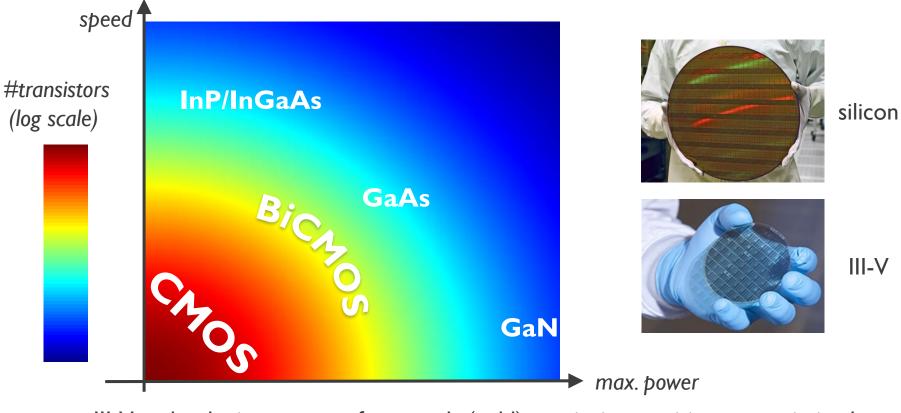


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#### Current landscape in foundry technologies

CMOS beats any other technology in integration level

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III-V technologies use very few metals (gold), extrinsic parasitics not optimized

# The 3D interconnect technology landscape

3D-SIP		3D-SIC	3D-SOC		3D-IC
Package stacking	Multi-die Packaging Interposer "2.5D" Embedded Die	Die Stacking µbump	Wafer-to-Wafer bonding	Wafer-to-Wafer Sequential Processing	Transistor Stacking
Interconnect Pitch scaling					
Imm 400µm	100 μm	l0 μm	Iµm I00nm Interconnect density (#/mm <sup>2</sup> )		
I IO	100 1000	) I 0 <sup>4</sup>	105	0 <sup>6</sup> I 0 <sup>7</sup>	108

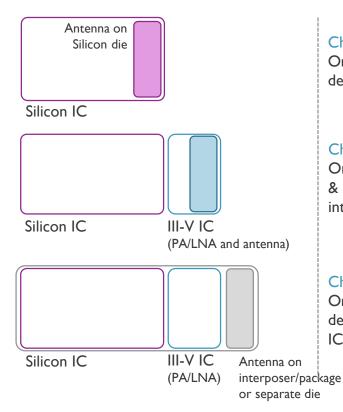
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#### ADC and DSP

- Baseband bandwidths grow to tens of GHz
  - ADCs in the tens of Gsps range are needed
  - Initially low spectral efficiency is required
  - But eventually move to ~64QAM or so → ~7 to 9 bits
- DSP speed must follow
  - Very high speed
  - Heavy parallelization
  - Multi-path is less frequent but can happen
  - Equalizer schemes must be revisited to cope with tens of Gbauds equalization
    - Digital vs analog
    - Pre- vs post equalization to bring complexity where it can be afforded (AP, BS)

### Chip-antenna co-design above 100GHz

#### EM and thermal challenges

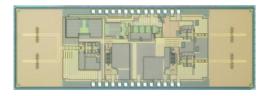


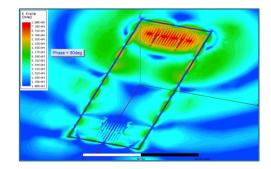
Challenge: On-chip antenna design in CMOS

Challenge: On-chip antenna design & low-parasitics IC/IC interconnect

#### Challenge:

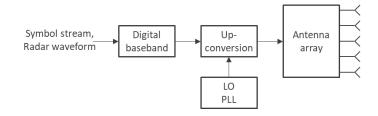
On-interposer antenna design & low-parasitics IC/IC interconnect I40 GHz FMCW radar, I0GHz BW, with antenna on chip, in standard 28 nm CMOS
(3 dB gain, I1dBm EIRP, 1 mm<sup>2</sup> area)



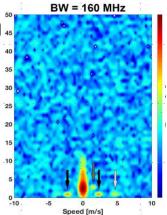


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#### Radar-Communications convergence



- Observation:
  - Radar and communications hardware, DSP and antennas are very similar
  - Radar and communications use more and more multiple antennas/MIMO concepts
  - Mm-wave comm (e.g. WiGig, 11ay at 60GHz) and mm-wave radar (automotive 77/79GHz) are well mastered technologies
  - Some wireless communications functionality have much in common with radar
    - Radar range profile vs channel estimation
    - MIMO radar vs MIMO channel estimation (channel between all possible TX-RX pairs) 45
  - Some developments and standardization already bridge the gap
    - Wi-Fi based people detection, fall detection
    - Some products, software stack appear (Origin Wireless, Cognitive Systems, Aura, ...)
    - Wi-Fi sensing (IEEE 802.11 SENS TIG/SG)



#### Radar-Communications convergence

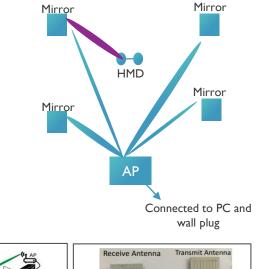
Green field for THz

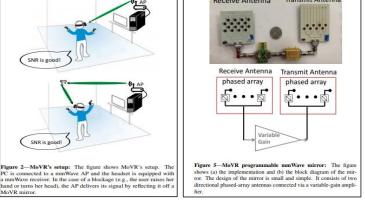
- But much more is possible
- Massive MIMO/large phased array systems can enable high angle resolution radar for target tracking and environment mapping
- Distributed massive MIMO can be turned into bistatic or multi-view radars
- Mm-wave/THz systems, with multi-GHz bandwidth, can have cm-scale range resolution
- Both functionalities can support each other for
  - Improved performance
  - Yet-to-discover new joint modes of operation

#### nLOS problem at mm-wave/THz

Robust coverage with Phased Array Mirror

- Using phased array based relays/re-routers to create alternate LOS path while maintaining low latency
  - Angle of incidence ≠ Angle of reflection
- Advantages
  - Overcomes blockage/shadowing
  - No Synchronization, handoff, and latency issues
  - Low cost and lower power alternative
- Challenges
  - Self-interference problem → full duplex design techniques
  - Multi-user

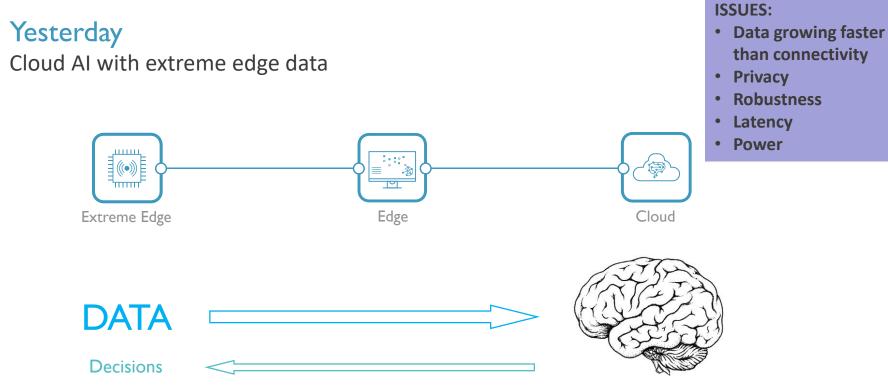




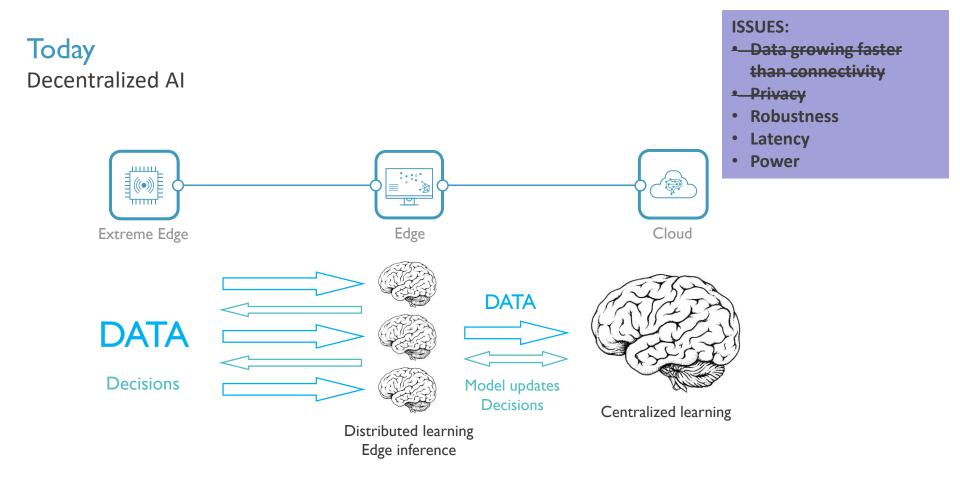
Source: Dina Katabi's MIT

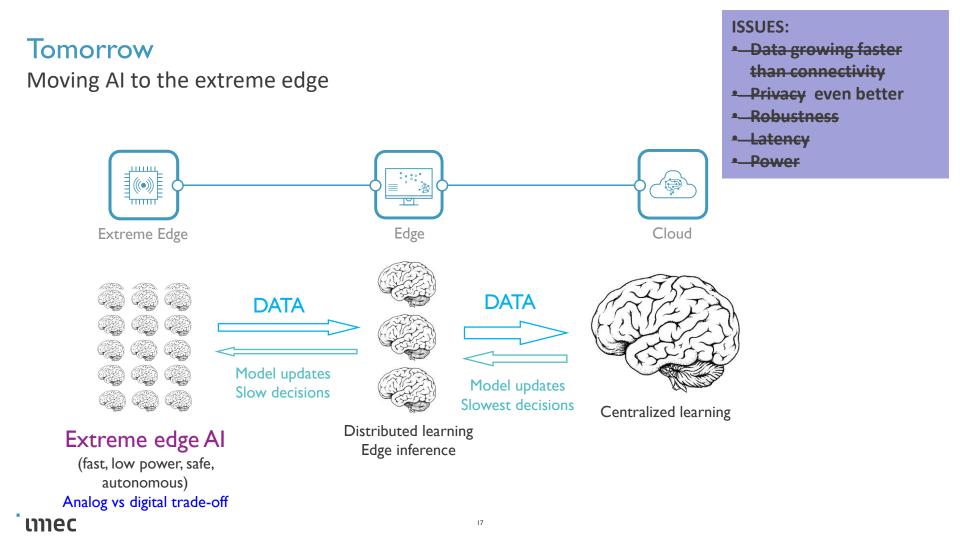
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#### Extreme Edge Processor



Learning & Inference



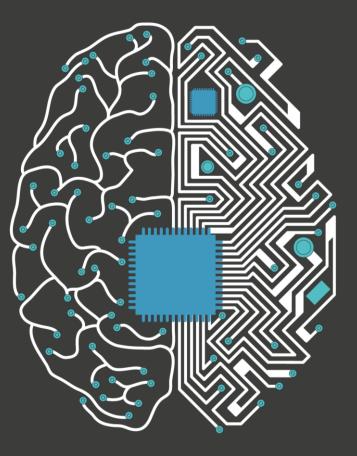


#### Neuromorphic Processor

Dimensions along which compute technologies can be neuromorphic

- Sequential vs. massively parallel
- Clocked vs. asynchronous
- Event-based processing
- Spiking NN
- Analog vs. digital
- Von-Neumann vs. non-Von Neumann (compute-in-memory)
- High-bit to Low-bit precision
- Learning from much labeled data vs. learning from little unlabeled data

#### This is NOT a traditional CPU/GPU/TPU/FPGA/ARM/... Limec



#### Conclusions

# Conclusions

#### Key research areas

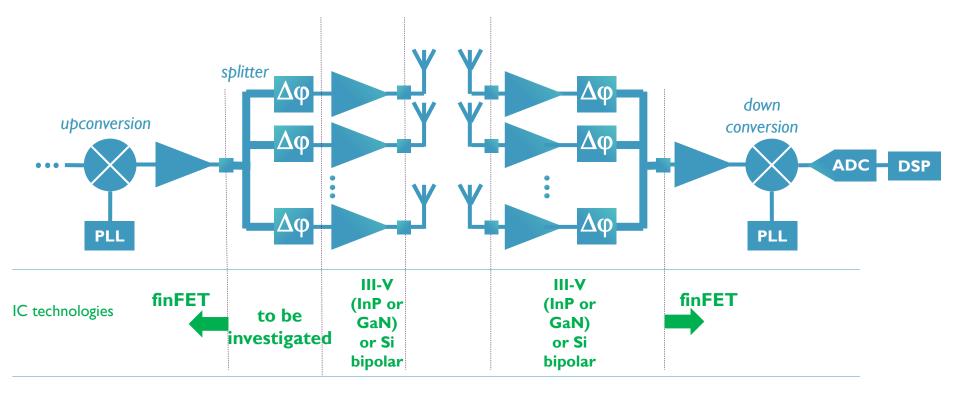
- Communications above 100 GHz at tens of Gbit/s call for:
  - Better devices for the RF part: III/V, III/N or GaN on CMOS
  - Faster ADCs, tens of Gsps, 7+ bits
  - Rethinking equalization schemes
  - Intelligent non-specular mirror might help in some cases
  - Chip-antenna co-design (antennas on chip become feasible)
  - Exploiting the third dimension for bonding/stacking
- Joint radar and communications
  - Leveraging massive arrays and mm-wave/THz bandwidth for high througput and high resolution
  - New joint modes of operation
- Extreme edge computing is a new paradigm calling for
  - A new breed of processor
  - New learning modes (mostly unsupervised)
  - Analog vs digital for extreme low power
  - Computing-connectivity tarde-off

#### ເກາຍດ

# embracing a better life

#### Back-up slides

#### CMOS cannot do it alone anymore



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# Marrying III-V with silicon?

Combine best of both worlds

- Several attempts to improve yield and economics of III-V
  - GaN on 300 mm Si wafers instead of GaN on SiC
- High-mobility III-V combined with CMOS
  - Monolithic, see
  - Challenge: overcome lattice mismatch, mismatch in thermal coefficients

Free-standing nano-ridges

E. Kunert et al., Compound Semiconductor, vol. 24, no. 5, July 2018.

Image: Compound Semiconductor, vol. 24, no. 5, July 2018.

Templated growth: full GaAs npn-HBT stack

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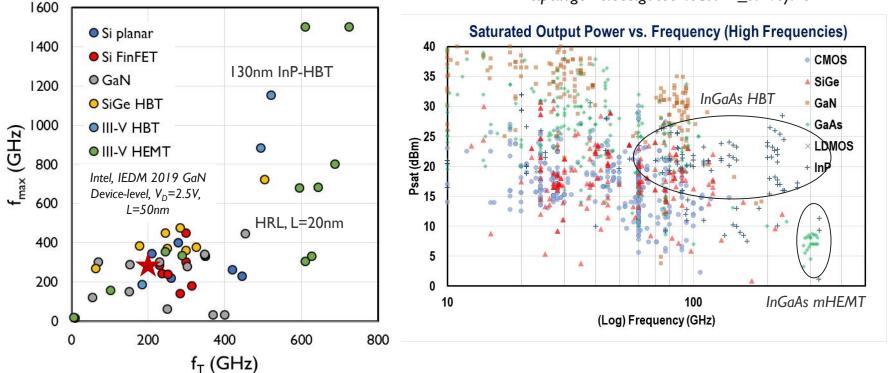
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Image: Compound Semiconductor

- Alternative: 3D combination of CMOS with III-V
  - Wafer-level hybrid bonding
  - Die-to-wafer, wafer-to-wafer, die-to-die
- Sequential 3D

### Which IC technology for > 100 GHz ?



III-V devices outperform Si(Ge) & GaN devices in speed, output power and efficiency > 100GHz

https://gems.ece.gatech.edu/PA\_survey.html